

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 08-248626  
 (43)Date of publication of application : 27.09.1996

(51)Int.Cl. G03F 7/004  
 G03F 7/039  
 H01L 21/027

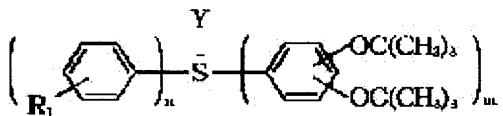
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## (54) CHEMICALLY SENSITIZED POSITIVE RESIST MATERIAL

## (57)Abstract:

PURPOSE: To provide a chemically sensitized positive resist material which has a high sensitivity against high energy beam radiation such as far ultraviolet rays, electron beam, and X-rays, and by which pattern formation can be made by developing it with an alkali aqueous solution, so that it is suitable for fine working technique.

CONSTITUTION: A chemically sensitized positive resist material is that which includes a new sulfonium salt as shown by the formula. In the formula, R<sub>1</sub> denotes a hydrogen atom, alkyl group, alkoxy group or dialkylamino group, and Y denotes trisulfomethanesulfonate or p-toluenesulfonate. The n is an integer of 0 to 2, m is an integer of 1 to 3, and n+m=3.



## LEGAL STATUS

[Date of request for examination] 27.04.2000  
 [Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3399141

[Date of registration] 21.02.2003

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]